S/109/60/005/008/012/024 E140/E355

Kinetics of Electron Motion in Secondary Emission from Thin Metal and Semiconductor Films

the present authors (Ref. 1). The results of this and subsequent studies are now explained as follows: the first characteristic depth is connected with the conditions of motion of secondary electrons. The second characteristic depth is related to the reflection of secondary electrons from the layer and the base. By suitable choice of pairs of base and film materials, information on kinetic factors of secondary electrons can be obtained. The fraction of back-diffusing electrons increases with increase of mean atomic number of the material, which facilitates the choice of pairs of materials for the various cases which may arise in these studies. Differences in secondary-emission factor measurements by other authors can be explained by the existence of these two characteristic depths. With d greater than the first characteristic depth, the film structure does not determine the shape of the secondary-emission factor versus depth curve.

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\$/109/60/005/008/012/024 E140/E355

Kinetics of Electron Motion in Secondary Emission from Thin Metal and Semiconductor Films

To determine the first characteristic depth it is necessary to take base and film materials with differing secondary. emission factors but equal back-diffusion factors. To determine the second characteristic depth, materials with differing back-diffusion factors should be chosen. Acknowledgments are made to M.T. Kostyshin for his assistance, There are 8 figures and 41 references: 22 Soviet and

ASSOCIATION:

Kiyevskiy gosudarstvennyy universitet imeni

T.G. Shevchenko Kafedra elektroniki

(Kiev State University imeni T.G. Shevchenko, Department of Electronics)

SUBMITTED:

December 21, 1959

Card 3/3

9,4300 (3005, 1164,1385)

21590

S/109/60/005/010/013/031 E032/E114

26. 24 21

Nakhodkin, N.G., and Nemtsev, V.P.

TITLE: Electron properties of thin films of germanium

PERIODICAL: Radiotekhnika i elektronika, Vol.5, No.10, 1960, pp. 1669-1671

TEXT: This paper was read at the 9th All-Union Conference on Cathode Electronics in Moscow, October, 1959.

The aim of the present work was to investigate the electrical conductivity of thin germanium films of various thicknesses and changes in the electrical conductivity due to heat treatment, oxidation, etc. In distinction to previously published work, the present authors state that they have carried out their measurements in "ultra-high vacuum" (p < 1.10-8 mm Hg). In ordinary vacua one always obtains p-type germanium films (owing to contamination by residual gas), while in ultra-high vacua n-type germanium films can be obtained. In the present experiments, n-type germanium films with o = 26,2 ohm cm were obtained. A special glass envelope was made which was used to measure the resistance of 12-13 films obtained in a single evaporation run. Silver contacts Card 1/4

21590

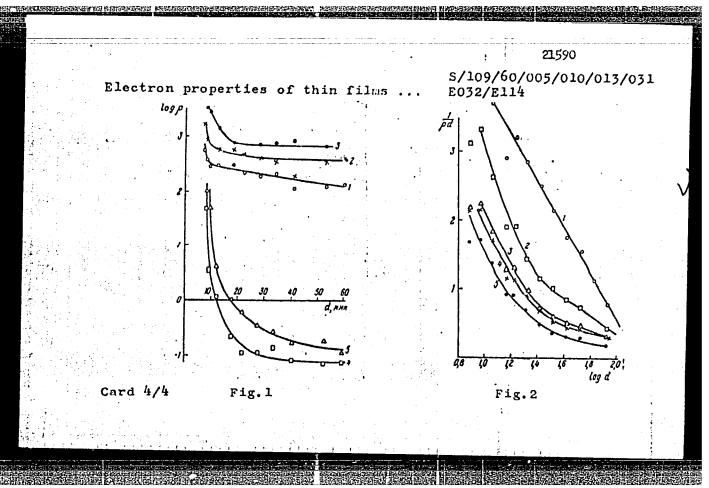
S/109/60/005/010/013/031

Electron properties of thin films. E032/E114

were employed and the thickness of the films was determined by calculation from the geometry and weight of the specimens. Fig. 1 shows the logarithm of the resistivity as a function of thickness (microns). In this figure, curve 1 refers to a freshly evaporated layer, curve 2 is for a specimen a few days old, curve 3 was obtained after heating at 300 °C for one hour, curve 4 after heating at 450 °C for one hour, and curve 5 after exposure to air. Fig. 2 shows dependence of 1/od on log d (1 - fresh deposit of Ge; 2 - oxygen atmosphere at 5 x'10-7 mm Hg for 15 min; 3, 4, 5 further exposure to oxygen). It is seen that a linear relationship is obtained between these two quantities for the freshly deposited film. It is concluded (in accordance with the J. Thomson theory, Ref. 4) that freshly deposited germanium films are continuous and uniform right up to 10 mm, since the change in the resistivity with thickness can be explained by the scattering of current carriers at the surface. This is confirmed by the fact that heating, oxygenation, etc. lead to a departure from the linear relationship. The mean free path of the current carriers in freshly deposited films of Ge was found to be approximately 100 mm, which is in agreement with the value calculated from the mobility. Card 2/4

21590
S/109/60/005/010/013/031
E032/E114
Electron properties of thin films of germanium
There are 2 figures, 1 table and 5 references: 3 Soviet and 2 non-Soviet.

ASSOCIATION: Kiyevskiy gosudarstvennyy universitet im.
T.G. Shevchenko
(Kiyev State University imeni T.G. Shevchenko)
SUBMITTED: December 21, 1959



APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R0011360200

9,4110(1140,1144,1331) 26,235P S/181/61/003/005/016/042 B136/B201

AUTHORS:

Nakhodkin, N. G. and Zykov, G. A.

TITLE:

Effect of oxygen on the electrical properties of an oxide

cathode at low pressures

PERIODICAL:

Fizika tverdogo tela, v. 3, no. 5, 1961, 1436 - 1444

TEXT: Insufficient attention has been paid in previous studies to the composition of residual gases in vacuum apparatus. The authors have therefore conducted a thorough investigation, in which the sealed apparatus has repeatedly been filled with oxygen and evacuated to pressures 10<sup>-8</sup> - 10<sup>-6</sup> mm Hg. The gas residue has been analyzed by means of an omegatron. First of all, two peaks have been observed at m = 16 and m = 32, accounting for 94% of the total amount. Comparative measurements with the 600 mass analyzer by the total amount. Comparative measurements with the 600 mass analyzer by G. Ya. Pikus have shown the m = 32 peak to be higher. A small nickel tube filled with barium peroxide served as an oxygen source. Two 3μ thick platinum probes were introduced into the oxide layers which had a thickness from 80 to 100μ. In addition to the cathode current, the measurements comprised conductivity, thermo-emf, and other electrical parameters. The cathode cur-

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Effect of oxygen ...

S/181/61/003/005/016/042 B136/B201

rent was measured at normal cathode temperatures with exponential pulses (f = 1 cycle), and at higher temperatures in d-c operation. Resistivity was determined from the potential drop between probe and core, depending upon the cathode current. The cathode temperature was determined by a calibration curve and by means of a thin thermocouple. Experiments have shown that both conductivity and thermionic emission current change almost in parallel and without delay during poisoning and reduction, i.e., almost all the oxide layers participate in both processes. Two mechanisms are referred to for an explanation: first, the oxygen is adsorbed on all exposed and fully developed grain surfaces of the oxide-layer, and splits into atoms, whereby the negative surface charge of the grains is augmented; this is accompanied by a decrease of the work function, and, consequently, of all other electrical parameters as well. Secondly, the diffusion of the oxygen ions or atoms into the grains, which is directly proportional to their surface concentration, reduces the number of oxygen vacancies which may act as donor centers. Taking account of diffusion provides an explanation for the experimental findings. N. D. Morgulis, Corresponding Member AS USSR, is thanked for his interest in the work. There are 7 figures and 34 references: 11 Soviet-bloc and 23 non-Soviet-bloc. The three most recent Card 2/3

Effect of oxygen ...

S/181/61/003/005/016/042 B136/B201

references to English-language publications read as follows: G. Higginson, Brit. J. Appl. Phys., 8, 148, 1957; 9, 106, 1958; N. A. Surplice, Brit. J. Appl. Phys., 10, 359, 1959.

ASSOCIATION: Kiyevskiy gosudarstvennyy universitet imeni T. G. Shevchenko, Kafedra elektroniki (Kiyev State University imeni T. G. Shevchenko, Department of Electronics)

SUBMITTED:

August 18, 1960 (initially) December 9, 1960 (after revision)

Card 3/3

# NAKHODKIN, N.G.; NEMTSEV, V.P. Device for investigating the relationship between the electric properties of thin condensed films and their thickness. Prib. i tekh.eksp. 6 no.4:113-116 J1-Ag '61. (MIRA 14:9) 1. Kiyevskiy gosudarstvennyy universitet. (Solid film-Electronic properties-Measurement)

NAKHODKIN, N.G.; MEL'NIK, P.V.

Photoeffect in the region of soft X rays. Radiotekh.i elektron, 6 (MIRA 14:16)

1. Kiyevskiy gosudarstvennyy universitet im. T.G.Shevchenko. (Photoelectricity) (X rays)

38914

24,6610

S/181/62/004/006/021/051 B104/B112

AUTHORS:

Nakhodkin, N. C., Ostroukhov, A. A., and Romanovskiy, V. A.

TITLE:

Inelastic scattering of electrons in thin layers

PERIODICAL:

Fizika tverdogo tela, v. 4, no. 6, 1962, 1514 - 1524

TEXT: Using a generalized model of continuous losses (T. Everhart. J. Appl. Phys., 31, 1483, 1960), a theory was developed for the inelastic single scattering of fast electrons within a double-layer target. The slowing down of the electrons in the target is described by  $\mathbf{v}^{\mathbf{n}}(\mathbf{x}) = \mathbf{v}_{\mathbf{0}}^{\mathbf{n}} - \mathbf{cgx}(1)$ , where  $\mathbf{v}_{\mathbf{0}}$  is the electron velocity at the surface of the target,  $\mathbf{v}(\mathbf{x})$  is the electron velocity after a distance  $\mathbf{x}$ ,  $\mathbf{g}$  is the target density, and  $\mathbf{c}$  is a slowing-down factor. The coefficient of inelastic scattering

 $\eta(y, a, p) = \frac{(a+p^2) a - 2p^6}{(a+2p^2) (a+p^2)} - a \left(1 - \frac{y}{p}\right)^{\frac{p}{p^2}} \left[\frac{1-p^2}{a+2p^2} \left(1 - \frac{y}{p}\right)^2 + \frac{2p^2}{a+p^2} \left(1 - \frac{y}{p}\right) - \frac{p^2}{a}\right], \tag{8}$ 

Card 1/3

S/181/62/004/006/021/051 B104/B112

Inelactic scattering of ...

and the energy distribution of the inelastically reflected electrons

$$\frac{d\eta}{d\left(\frac{E}{E_0}\right)} = \frac{4}{a+1} \frac{E}{E_0} \left\{ 1 - \left[ 1 + \frac{a}{2} \left( 1 - \frac{E^2}{E_0^2} \right) \right] \times \left( \frac{1 + \frac{E^2}{E_0^2}}{2} \right)^a \right\} \left( 1 - \frac{E^2}{E_0^2} \right)^{-2}.$$
(19)

are derived. Here, y = x/R; x is the thickness of the target; R is the distance determined by (1) with n = 4 and  $p = \cos \vartheta$ ;  $\vartheta$  is the angle of incidence; and  $a = \Im Z^2 e^4 N_A/m^2 Ac$ . The theory is applicable to light elements ( $Z \le 30$ ). In high-density substances it is necessary to allow for multiple collisions. Experimental results agree well with estimates using the above formulas. There are 8 figures.

Card 2/3

Inelastic scattering of ...

S/191/62/004/006/021/051 B104/B112

ASSOCIATION: Kiyevskiy gosudarstvennyy universitet im. T. G. Shevchenko (Kiyev State University imeni T. G. Shevchenko)

SUBMITTED:

January 25, 1962

Card 3/3

144.95

8/181/63/005/001/006/064

B102/B186

AUTHORS:

Nakhodkin, N. G., Ostroukhov, A. A., and Romanovskiy, V. A.

Scattering of electrons passing through thin films

TITLE:

Fizika tverdogo tela, v. 5, no. 1; 1963, 41-47

PERIODICAL:

11.00

19 0112

TEXT: Using the model of continuous energy losses (cf. T. Everhart, J.Appl.Phys., 31, 1438, 1960), the authors have already studied the inelastic reflection of electrons. Here the same method is followed in order to study the passage of fast electrons through free films, and to calculate the transmissivity coefficients  $\eta$ , assuming single elastic scattering through a large angle.  $\eta$  is the flux ratio of electrons passing through to incident electrons. In the simplest case of Rutherford scattering

 $\eta = (1-d)^{-a} \exp(-2ad)/(1-d)$  is obtained, where  $a = \pi Z^2 e^4 N_a/m^2 Ac$ , and  $N_a$ is Avogadro's number. Putting a = 0.045Z gives a close approximation. d = t/R is the dimensionless thickness of the film. For films of equal thickness, but with different incident electron energies Eo, the expression

Card 1/3

S/181/63/005/001/006/064 B102/B186

Scattering of electrons passing through ...

$$\eta = \left[1 - \left(\frac{E_{0k}}{E_0}\right)^2\right]^{-4} \exp\left[-\frac{2\sigma\left(\frac{E_{0k}}{E_0}\right)^2}{1 - \left(\frac{E_{0k}}{E_0}\right)^2}\right]. \tag{9}$$

holds. These energies are expressed in terms of  $E_0/E_{\rm ok}$ , where  $E_{\rm ok}$  is the energy of electrons with a range equal to the thickness of the film. The function I(y) (cf. Phys.Rev.,98,1597,1955) is given near  $y\sim 1$  by  $I(y)\sim (1-y)^{\gamma}\exp(-A/(1-y))$ , where  $\gamma$  and  $\Lambda$  are constants depending on the shape of the source and on the initial electron energy; y=x/R,  $R=v_0^4/c_0$ . The following holds near  $y\sim d\sim 1$ :  $I(y)\sim (1-y)^{-a-3/4}\exp(-2a/(1-y))$ .  $\eta$ , was measured as a function of various parameters for various metals and for electrons of various energies in the kev range, and the curves obtained were compared with the theoretical values. It follows from the results that the theoretical principles obtained are general, i.e. that the curves are normalizable. The dependence of the  $\eta$  of a two-layer film on its  $180^{\circ}$  orientation relative to the electron beam was detected experimentally using an  $\Lambda 1$ -Au film. The ratio of the extrapolated range to the total

Card 2/3

S/181/63/005/001/006/064 B102/B186 Scattering of electrons passing through ...

range depends on the material. The total range R can be determined by linear extrapolation of the  $\eta(t)$  curves to the abscissa ( $\eta=0$ ). There are

ASSOCIATION: Kiyevskiy gosudarstvennyy universitet im. T.G. Shevchenko (Kiyev State University imeni T.G. Shevchenko)

SUBMITTED: July 16, 1962

Card 3/3

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	/ /SWT(1)/EWG(k)/BDS AFFTC/ASD/ESD-3/IJP(C) Ps-4/Pz-4
	L 18576-63 EFR/EWA(h)/EWT(1)/EWG(k)/BDS AFFTC/ASD/ESD-3/10F(0)
	WM/AT 8/0181/63/005/006/1/32/7/O
	4 11 D V
	tenth of the photoelectric
	TOPIC TAGS: photoelectric effect, Andrews alectron, photoemission
	the investigated material
	measurements of and KC1) was sprayed in words am of Hg. The thickness of
	perimental devices at each point and controlled by the energy of quanta are shown
	perimental device at a vacuum of about 5 % perimental device at a vacuum of a vacuu
	wedge was computed. The relations of effective depth is associated with the mean in Table 1 (see Enclosure 1). It is concluded that the observed results may in Table 1 (see Enclosure 1). It is concluded that the associated with the mean in Table 1 (see Enclosure 1) and the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the explained if it is assumed that the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the mean explained if it is assumed that the effective depth is associated with the explained if it is assumed that the effective depth is associated with the explained if it is assumed that the effective depth is associated with the explained in the explained in the effective depth is associated with the explained in
	free path of fact the fact that the fact the fact that the fact that the fact that the fact that the
	Card 1/3

	L 18576-63 ACCESSION NR: AP3001300  the thickness dependence of the photoelectric effect produced by soft x-rays thus permits the determination of the emergent region of slow secondary electrons coming from fast photoelectrons, and also the effective depth of photoemission, which is established by the mean free path of fast photoelectrons. Orig. art. has: 2 figures and 1 table.
	ASSOCIATION: Kiyevskiy gosudarstvenny*y universitet (Kiev State University)
i i	SUBMITTED: 29Dec62 DATE ACC: 01 Tul63
	ENCL: 01
	SUBMITTED: 29Dec62 DATE ACQ: 01Jul63 ENCL: 01 SUB CODE: PH NO REF SOV: 009 OTHER: 002
	SUB CODE: PH NO REE SOV. 000

NAK HODKIN, N.G.; MEL'NIK, P.V.

Energy distribution of secondary electrons and photoelectrons generated by soft X rays. Fiz. tver tela 5 no.9:2441-2447 S '63. (MIRA 16:10)

1. Kiyevskiy gosudarstvennyy universitet, kafedra elektroniki.

S/109/63/008/002/015/028 D266/D308

AUTHORS:

Nakhodkin, N.G. and Nel'nik, P.V.

Kinetics of electron motion in solids excited by

TITLE: soft X-rays

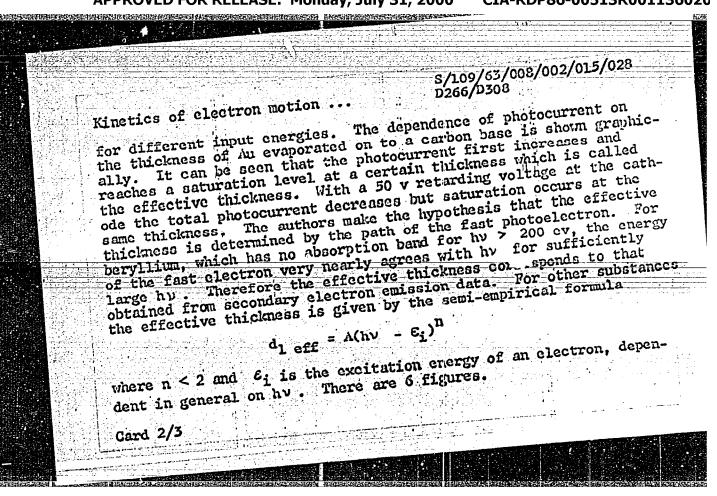
PERIODICAL:

Radiotekhnika i elektronika, v. 8, no. 2, 1963,

303-310

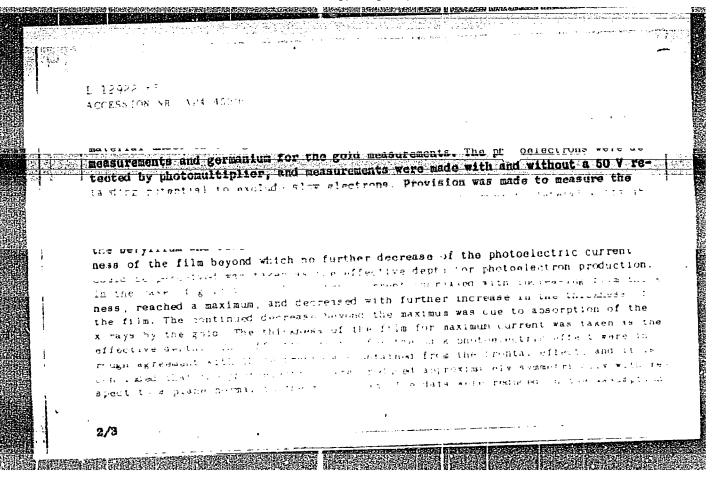
TEXT: For the energy range 100 to 600 ev, monochronatic incident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation was obtained with the aid of a diffraction gratineident radiation g incident radiation was obtained with the aid of a diffraction grating. For larger energies (hu > 1000 ev) filters were used resulting in an incident radiation at hu = 1.2, 4 and 8 kev. The samples investigated were of Au, Ag, Ge, Be, and KCl. In order to avoid investigated were of Au, Ag, Ge, Be, and kCl. In order to avoid attenuation in air both the X-ray sources and the detector (photo-attenuation in air both the X-ray sources and the detector (photo-multipliers) were in vacuum, in a common envelope. Measuring the photocurrent for thin layers of KCl and Au by applying a retarding photocurrent for thin layers of the electrons were slow, as in secfield it was found that most of the electrons committed from ondary electron emission. The mean energy of electrons emitted from the conditions and the conclusions qualitatively agreed than for Au. These conclusions qualitatively agreed

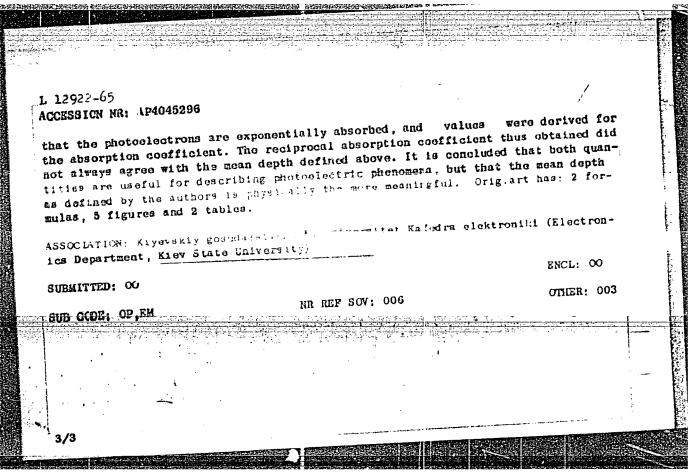
Card 1/3



	S/109/63/008/002/015/028 lectron motion D256/D308  Kiyevskiy gosudarstvennyy universitet im. T.G. Shev- chenko (Kiyev State University im. T.G. Shevchenko)			
ASSOCIATION:				
SUBMITTED:	March 19, 1962			
		gatak kebalan dal <b>a</b> kerala. Kabupatan		
Card 3/3			,	

	L 12922-65 EWT(1)/EWG(k)/EWT(m)/EEC(t)/EWP(t)/EWP(n); Pz-6 IJP(c)  LD/IG/AT SSD/AFWL/ASP(a) S/2FSTR/ESD(se)/SSD(*) 5/0048/64/028/009/1436/1443
	AUTHOR: Wakhodkin, N.G.; Wel'nik, P.V.
ŗ	TITLE: Rear photoelectric effect, x-ray, photoelectron, electron absorption
	ABSTRACT: The photoelectric current from the rear face of beryllium and gold films, excited by x-rays incident on the front face and traversing the film was measured as a function of the thickness of the film. These measurements of the rear photoelectric effect were undertaken to clarify discrepancies between conclusions concerning the mean paths of photoelectrons within the metal previously crawn from frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements by the authors (Radiotekhnika i elektron-frontal photoelectric effect measurements) in the measurements in the
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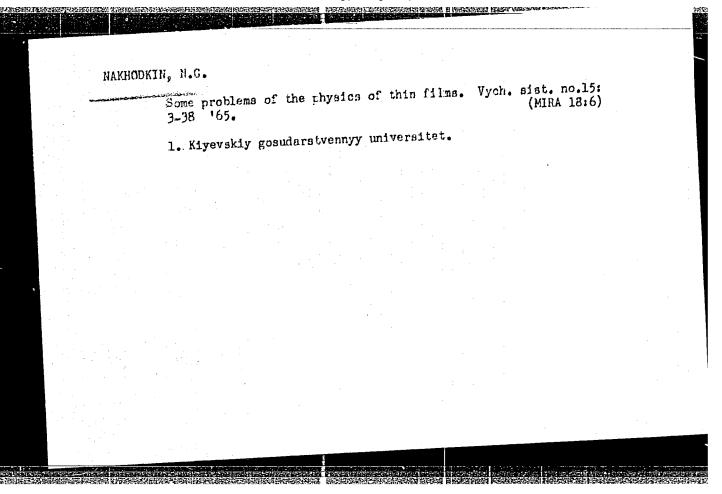




OSTROUKHOV, A.A.; NAKHODKIN, E.C. [Nakhodkin, N.H.]

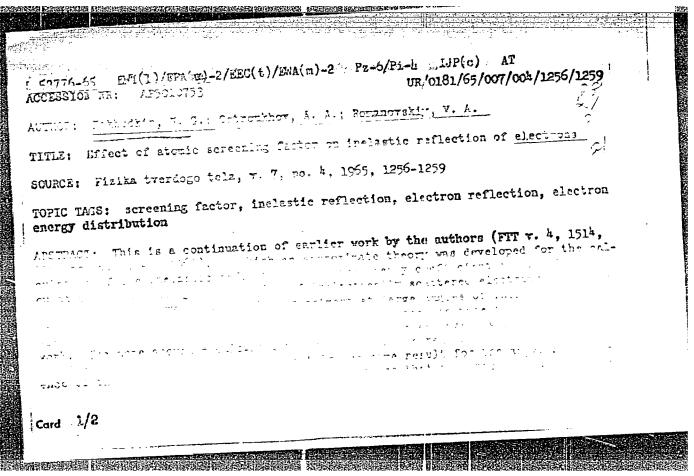
Approximate calculation of the paths of relativistic electrons from the stopping power of a substance. Ukr. fiz. zhur. 9 nc.10: 1151-1153 0 '64 (MIRA 18:1)

1. Kiyevskiy gosudarstvennyy universitet im. Shevchenko.



Inelastic electron scattering in thin films. Fir. tver. tela
7 no.1:210-216 Ja '65.

1. Kiyevskiy gosudarstvennyy universitet imeni Shevchenko.

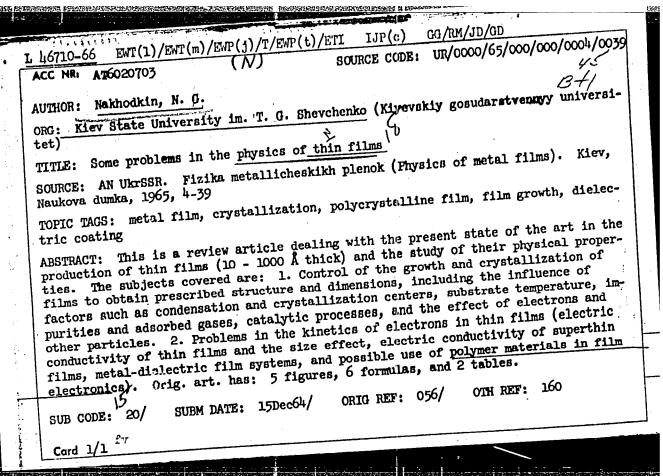


Conscionated ablacementalisms. Lateral by Lateral Date and Date an L 52776-65 APS010753 ACCESSION KR: ing does not change essentially the previous results for the engular dependence of the elastic reflection coefficient, and the discrepancy at large angles still remains. Even if further calculations show that the effective cross section at small acattering angles must be modified, the influence of the atomic form factor on the angular dependence of the elastic refraction coefficient should not be large. Orig. art. has: 2 figures and 3 formulas. ASSOCIATION: Kiyevskly gogudarstvennyy universitet im. T. G. Shevchenko (Kiev State University) SUB CODE: NP 00 ENCL SUBMITTED: 17Kov64 OTHER: 005 HR REF SOV:

OSTHOUKHOV, A.A.; NAKHODKIN, N.G.

Approximate analytic expression for the run of particles relarded according to Bethe's law. Radiotekh. 1 elektron. 10 no.3:522-529 (MIRA 18:3) Mr 165.

1. Kiyevskiy gosudarstvennyy universitet im. T.G. Shevchenko.



NAKHODKIN, V.M.; GORCHAKOVA, O.D., red.; NIKOL'SKAYA, K.G., tekhn.

[Forces acting on the train; lecture on the subject "Electric train traction" for students of the advanced special courses of the "Electrification of railroad transportation"] Sily, deistvuiushchie na poezd; lektsiia po disportation "Elektricheskaia tiaga poezdov" dlia studentov tsipline "Elektricheskaia tiaga poezdov" dlia studentov starshikh kursov spetsial nosti "Elektrifikatsiia zheleznostarshikh kursov spetsial nosti "Elektrifikatsiia zheleznodorozhnogo transporta." Moskva, Vses. zaochnyi in-t inzhenedorozhnogo transporta, 1963. 23 p. (MIRA 17:4)

NAKHODKINA, L. G.

"Vegetative Innervation Characteristics of Animals Suffering From Transinjected
"Vegetative Innervation Characteristics of Animals Suffering From Transinjected
(KL, No 1, Jan 55)

Survey of Scientific and Technical Dissertations Defended at USSR Higher
Educational Institutions (12)
SO: Sum. No. 556, 24 Jun 55

T-5

NAKHODKINA, L.G.

USSR/General Problems of Pathology - Tumors.

Abs Jour :

: Ref Zhur - Biol., No 3, 1958, 12691

Author

: Nakhodkina, L.G.

Inst

: Not given

Title

: On Peculiarities of the Autonomic Reactions in Animals

With Transplanted Cancer.

Orig Pub

: Uch. zap. Leningr. gos. ped. in-t, 1956, 19, 117-139

Abstract

: During the first period of development of the BrownPeerce tumor in rabbits there was hypotension and sinus
bradycardia; this attests to the increased excitability
of the vagus centers. At the same time there was an increased tonus, but to a lesser degree, of the sympathetic
creased tonus. The latter's tonus became greatly increased
during the second period (tachycardia, hypertension and
an elevated skin temperature). During this period

Card 1/2

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-0

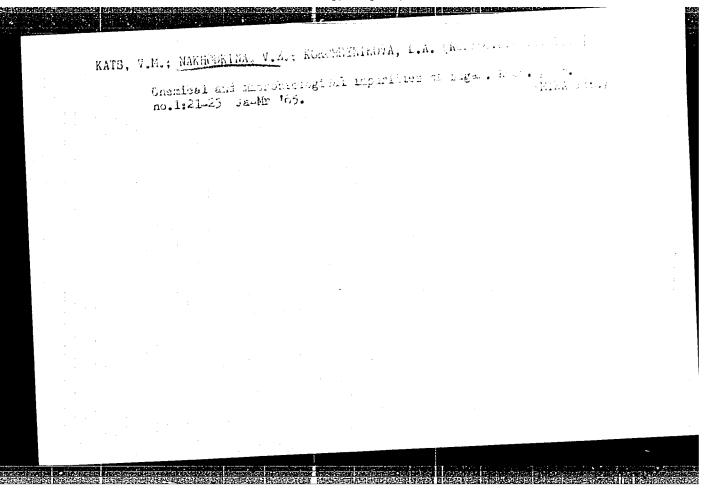
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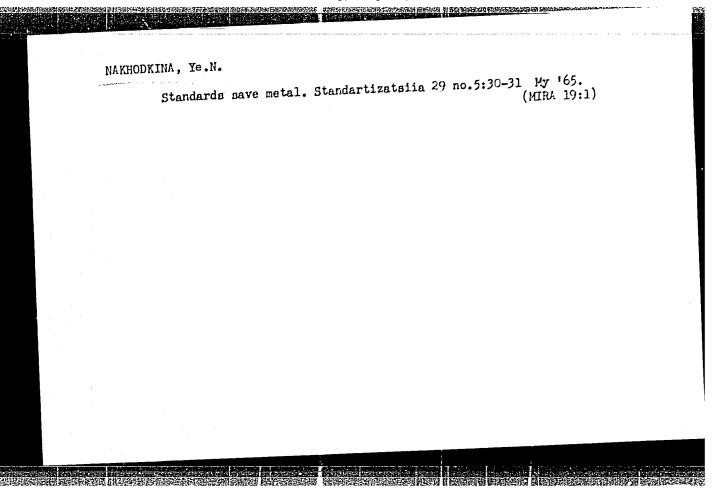
NAKHODKINA, L.G.; YEVDOKIMOV, S.A.

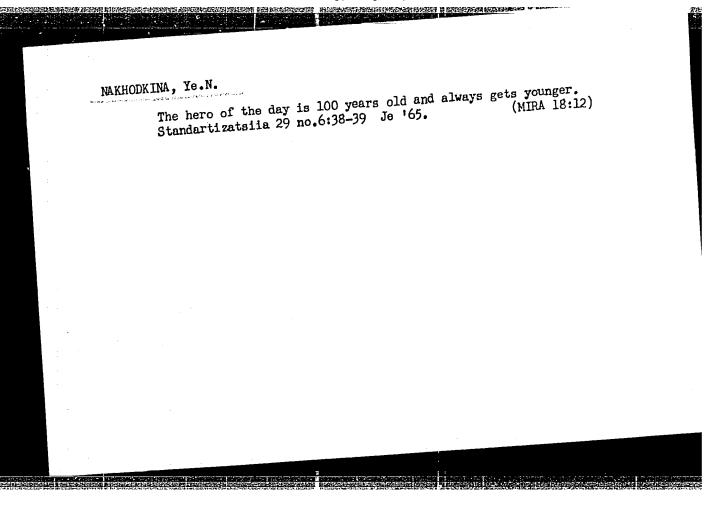
Apparatus for the intracellular lead off of electrical potentials.

Fiziol.zhur. 45 no.6:716-717 Je '59. (MIRA 12:8)

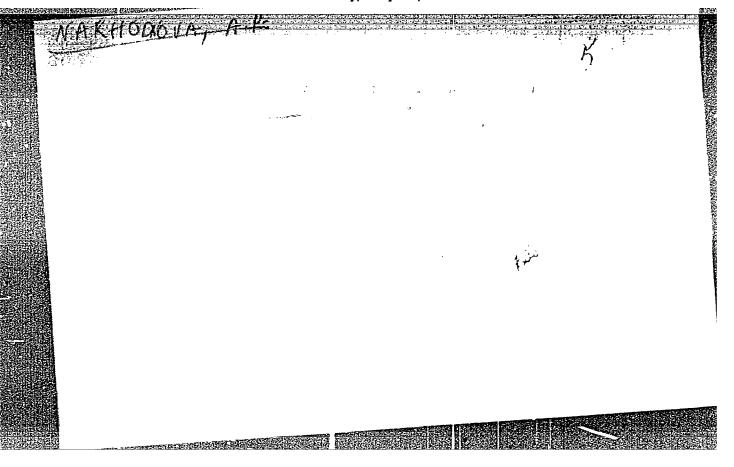
1. From the department of physiology and anatomy, A.I.Herzen
Paedagogical Institute, Leningrad.
(NEUROPHYSIOLOGY, appar. & instruments
appar. for intracellular derivation of
electrical potentials (Rus))







NAKHODNOVA, A. P Name: NAKHODNOVA, A. P. Dissertation: The electric conductivity, dielectric permeability, and dielectric losses of oxides and haloid compounds of elements of group II and the energy of the crystal lattice Cand Tech Sci Degree: Min Higher Education USSR, Tomsk Order of Labor Red Banner Polytechnic Inst imeni S. M. Kirov ense Date, Place: 1956, Tomsk Source: Knizhnaya Letopis', No 47, 1956



SOY/112-58-2-1859

Translation from: Referativnyy zhurnal, Elektrotekinika, 1958, Nr 2, p 9 (USSR)

AUTHOR: Nakhodnova, A. P.

TITLE: Electric Properties of Ionic Compounds of the Second-Group Elements in Connection with the Crystal-Lattice Ionic Interaction Energy (Elektricheskiye svoystva ionnykh soyedineniy elementov II gruppy v svyazi s energiyey vzaimodeystviya ionov v kristallicheskoy reshetke)

PERRODICAL: Izv. Tomskogo politekhn. in-ta, 1956, Vol 91, pp 209-218

ABSTRACT: Conductivity & of sintered polycrystalline specimens of chemically pure oxides and haloid compounds of Mendeleyev's second group of elements and also & and tg 6 have been measured in a vacuum of 10-5 mm of mercury column. The specimens, disks 10-16 mm diameter and 0.35-0.8 mm thick, were calcined for two hours in a silit furnace. Platinum and silver electrodes were used. Conductivity & has been measured on DC, & and tg & at 450-900 kc. Measurements of & and tg & of oxides have been made at 1550-480°C, of halogen compounds at 25°-255°C. All compounds have shown an increase (characteristic to ionic conduction) in electric conductivity with temperature. Electrical

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SOY/112-58-2-1859

Electric Properties of Ionic Compounds of the Second-Group Elements in . . . .

properties of Mendeleyev's second group of elements, viz.,  $\theta$ , current-carrier activation energy,  $\mathcal{E}$ , and tg $\mathbf{S}$ , are all closely associated with physical properties of the substance;  $\theta$  increases with decreasing energy of crystal lattice. Bibliography: 10 items. Tomskiy politekhnich. in-t (Tomsk Polytechnic Institute), Tomsk.

A.A.V.

Card 2/2

24(6) AUTHORS: .

Vorob'yev, A. A., Makhodnova, A. P.

SOV/57-28-10-11/40

TITLE:

High-Frequency Dielectric Losses and the Lattice Energy in Compounds of Second Group Metals (Dielektricheskiye poteri na vysokov chastote i energiya reshetki dlya soyedineniy

metallov vtoroy gruppy)

PERIODICAL:

Zhurnal tekhnicheskoy fiziki, Vol 28, Nr 10,

pp 2173 - 2174 (USSR) 1958

ABSTRACT:

This paper gives an account of the investigation of the temperature and frequency dependence of the tg (loss angle) of sintered polycrystalline samples of oxides, fluorides and chlorides of second group metals. BeO, MgO, CaO, SrO, and BaO were investigated in a temperature range of 25:480°C, Ca-, Sr-, Bafluorides and Ca-, Sr-, Ba-chlorides in a temperature range of 25 to 260°C. The samples were produced from chemically pure substances. The density of the samples amounted to 65-70% and 95%, respectively, of the density of the monocrystals, ty 8 decreases in all poly-

Card 1/3

crystalline sintered samples of all compounds in the

High-Frequency Dielectric Losses and the Lattice Energy SOV/57-28-10-11/40 in Compounds of Second Group Metals

total range of frequencies and temperatures employed with an increase of the lattice energy. The growth of the cation radius under otherwise equal conditions is accompanied by a relaxation of the lattice and by a modification of the tg which proceeds according to certain regularities. The variation of the  $t_{\mathcal{G}}$   $\delta$  in halide compounds of alkaline earth metals corresponds to the fundamental physical and chemical properties of the substance in porous and in dense samples. It is determined by the energy of the thermochemical interaction of the ions of the crystal lattice. The information gained in the investigation of the frequency dependence of the dielectric losses in the oxides and halide compounds of the elements of the second group indicates that in the range of 450 to 900 kc the losses are reduced, when the frequency rises. The alelectric losses in porous polycrystalline samples of compounds of the second group of elements in air are considerably in excess of those in vacuum. In samples prepared of chemically pure substances the tg & varies as the cation dimensions, the

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High-Frequency Dielectric Losses and the Lattice Energy SOV/57-28-10-11/40 in Compounds of Second Group Metals

polarizability and inversely as the point of fusion of the substance. The smaller the energy of the crystal lattice the higher will be the losses at a given temperature and frequency. G.V.Krivoshchekov, Candidate of Technical Sciences, assisted with the work. There are

2 figures.

SUBMITTED:

November 4, 1957

Card 3/3

Vorob'yev, A. A., Nakhodnova, A. P. 24(6) AUTHORS:

507/57-28-10-14/40

TITLE:

Electric Conductivity and Lattice Energy of Compounds of the Metals of the Second Group of D.I. Mendeleyev's System (Elektroprovodnost' i energiya reshetki soyedineniy

metallov vtoroy gruppy sistemy D.I.Mendeleyeva)

PERIODICAL:

Zhurnal tekhnicheskoy fiziki, Vol 28, Hr 10,

pp 2192 - 2193 (USSR), 1958

ABSTRACT:

This paper gives an account of the study of the problem, whether the laws derived for monocrystals are applicable also to polycrystalline bodies used in engineering. The temperature dependence of the electric conductivity of oxides and halide compounds of the second group elements in the temperature range of 250 to 900°C was measured. The polycrystalline camples were prepared by pressing and subsequent baking in the air. The measurements were carried out in vacuum with direct current in weak fields (2.) to 75 V/cm) at a pressure of  $p = 10^{-5} mm$  of mercury column. Platin electrodes were evaporated onto the samples. It appears that at high temperatures the

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Electric Conductivity and Lattice Energy of Compounds SOV/57-28-10-14/40 of the Metals of the Second Group of D.I.Mendeleyev's System

electric conductivity of sintered oxides of second group metals decreases with an increase of the lattice energy, whereas the activation energy increases. Identical phenomena were also observed with other compounds. The specific electric conductivity of the second group metal oxides, of the calcium-, strontium-, and barium fluorides, and of the calcium-, strontium-, and barium chlorides varies as the atomic volume of the metal, the polarizability of the cation, the decrease of the point of fusion of the compound, the dissociation energy and the magnitude of the isobaric potential. Hence the most simple compounds of the second group elements exhibit, besides the modification of the principal thermochemical features, a variation of the specific electric conductivity, which is governed by definite rules. In the range of low temperatures the activation energy of all compounds is considerably deficient of that in the range of high temperatures and lies within the limits of 0.15 to 0.58 eV. The variation of the specific conductivity and of the activation energy in

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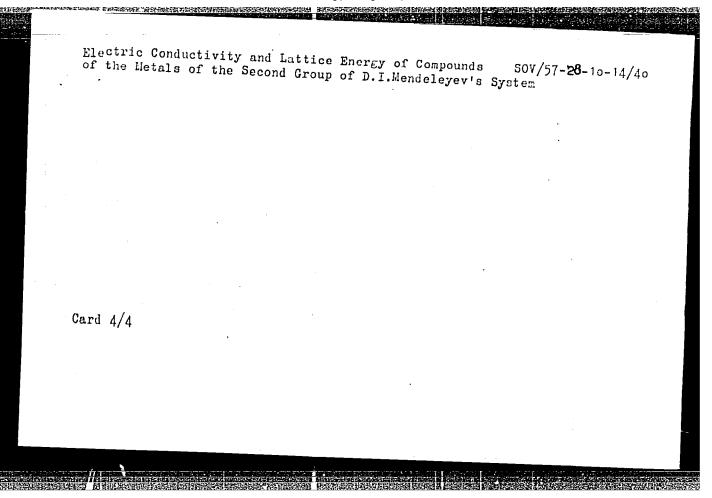
Electric Conductivity and Lattice Energy of Compounds SOV/57-28-10-14/40 of the Metals of the Second Group of D.I.Mendeleyev's System

the range of relatively small temperatures does not show a course which is distinctively governed by definite rules. Hence the activation energy and the specific conductivity in the range of high temperatures are determined by the binding energy of the ions in the lattice and can be used as a characteristic feature of the electrophysical properties of the substances. G.V. Krivoshchekov, Candidate of Technical Sciences, assisted with the work. There are 2 figures.

SUBMITTED:

November 4, 1957

Card 3/3



VOROB'YEV, A.A.; NAKHODNOVA, A.P.

Dielectric losses in oxides and of elements of the 2d group. Izv.
(KIRA 14:9)
TPI 95:306-313 '3.
(Halides--Electric properties) (Oxides--Electric properties)

15.2210

SOV/112-60-1-1156

Referativnyy zhurnal Elektrotekhnika, 1960, Nr 1, p 15 5,4100 Translation from:

(USSR)

AUTHORS:

Vorob'yev, A.A., Nakhodnova, A.P.

TITLE:

Electroconductivity of Oxides and Haloid Compounds of the II

Group Elements

PERIODICAL:

Izv. Tomskogo politekhn. in-ta, 1958, Nr 95, pp 325 - 330

ABSTRACT:

The study of specific conductivity 6 was carried out on caked polycrystalline disks 10 mm in diameter and 0.35 - 0.8 mm thick. The relative density of samples was 65 - 75%. The samples were ground and platinized. Measurement of temperature dependence of 5 was carried out by the residual current at 10-5 mm Hg. In the weak field region (E = 2.5 - 75 v/cm) 5 of the compounds under study increases with an increase of E. With an increase under study increases with an increases. For a given temperature, in the density of samples of increases.

Card 1/2

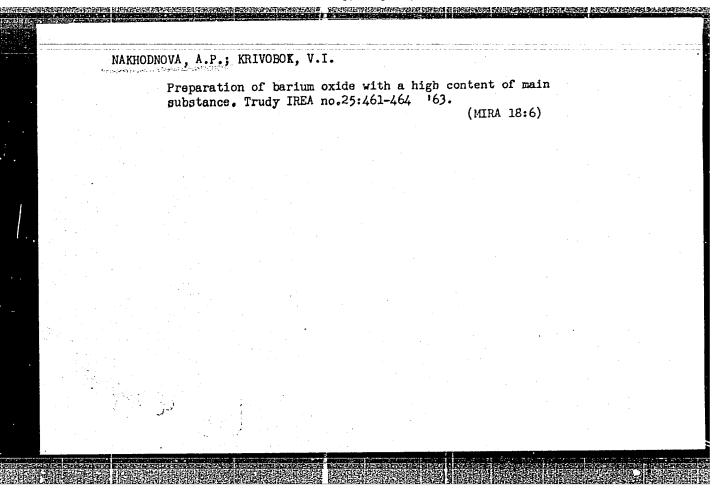
SOV/112-60-1-1156

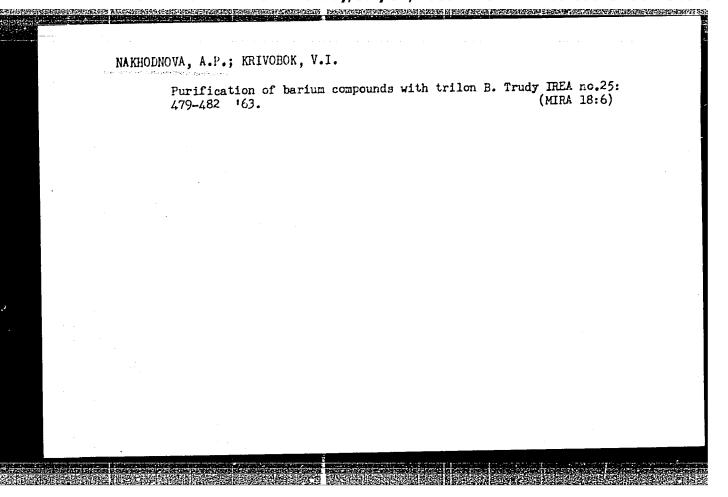
Electroconductivity of Oxides and Haloid Compounds of the II Group Elements

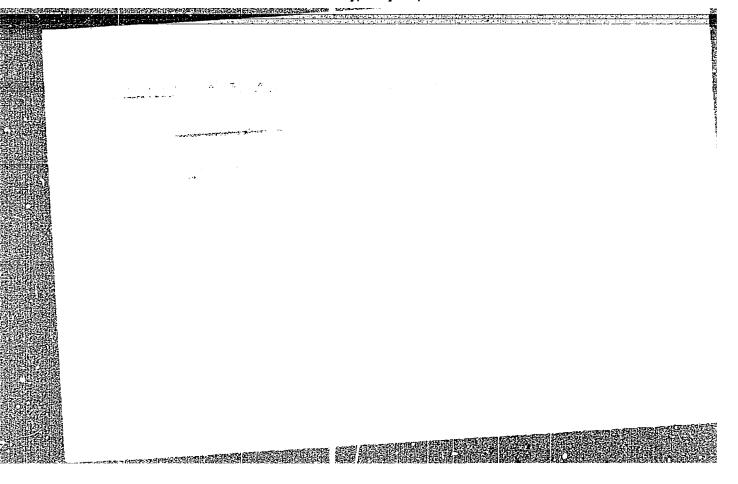
of oxides and haloid compounds increases with a decrease in the energy of the crystalline lattice. The activation energy of charge carriers decreases with a decrease in the energy of the crystalline lattice.

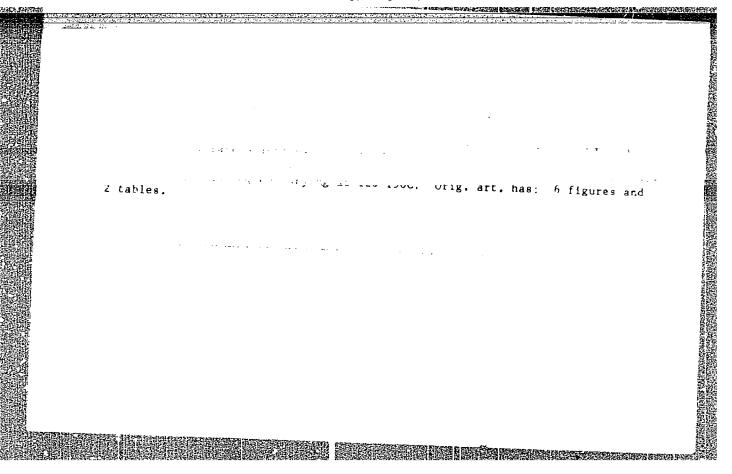
A.A.V.

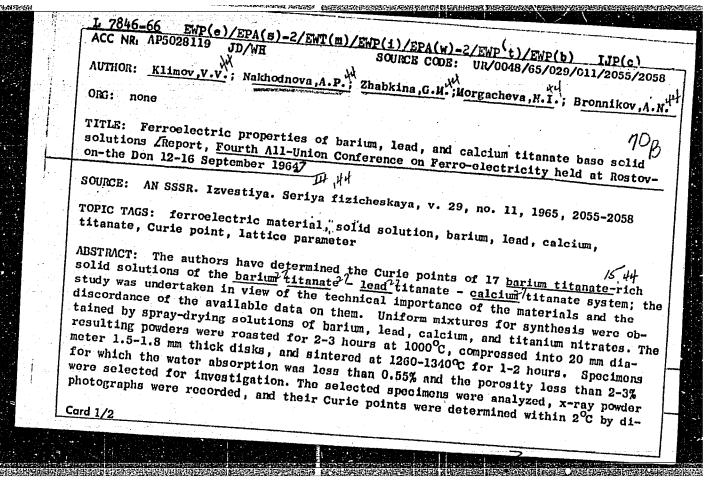
Card 2/2











L 7846-66

ACC NR: AP5028119

electric constant measurements. It was found that the Curie point increased with decreasing barium content when either the calcium content, the lead content, or their ratio was held constant. When the barium content was held constant the Curie point increased with increasing lead content. The variation of the Curie point with composition in the region of relatively high calcium content differed from that found by McQuarry (J.Amer.Ceram. Soc., 40, No. 2, 35 (1957)) and T.Ikeda (J.Phys.Soc. Japan, 3, No. 4, 335 (1958)), the present measurements giving the higher Curie points in this region. The solid solutions with the higher Curie temperatures had unit cells with larger volumes and, in agreement with the findings of McQuarry and Ikeda (loc.cit. supra), higher degrees of lattice tetragonality. The increase of the Curie temperature with increasing calcium, decreasing barium, and constant lead content contradicts the current opinion that the Curie temperatures of ferroelectrics with the perovskite structure are increased by increasing the volume and polarizability of the ions at the A-sites in ABO3 crystals. The discrepancy between the present results and those obtained by other authors with single compounds and binary systems is obviously to be explained by the fact that the laws governing the behavior of three-component systems containing A-type ions with different electronic structures are more complex than those applicable to binary systems. The discovery of these laws will require further investigation. Orig. art. has: 5 figures and 1 table.

SUB CODE: SS, EM

SUBM DATE: 00/

ORIG. REF: 003 OTH

OTH REF: 006

Card 2/2

AP6029031

SOURCE CODE: UR/0413/66/000/014/0042/0042

INVENTORS: Klimov, V. V.; Androyev, A. Ya.; Nakhodnova, A. P.; Kozachenko, V. N.; Akhkozov, Ye. A.; Ivanov, D. G.; Didkovskaya, O. S.; Zvonik, V. A.

ORG: none

TITLE: A method for obtaining a piezoceramic material. Class 21, No. 183812 Zannounced by Donets Branch of All-Union Scientific Research Institute of Chemical Reagents and of High Purity Chemicals (Donetskiy filial Vsesoyuznogo nauchnoissledovatel skogo instituta khimichoskikh reaktivov i osobo chistykh khimichoskikh veshchestv)\_/

SOURCE: Izobret prom obraz tov zn, no. 14, 1966, 42

TOPIC TAGS: piezoelectric ceramic, barium compound, lead compound, calcium compound, titanium compound, sintered alloy

ABSTRACT: This Author Certificate presents a method for obtaining a piezoceramic material from a mixture of barium, lead, calcium, and titanium compounds by sintering this mixture. To lower the temperature of sintering this material, the above compounds are used in the form of nitric acid solutions of barium, lead, calcium, and titanium. This solution is atomized in a stream of air at the temperature of 400-500C. After this, the powder is sintered at the temperature of 800-1000C. SUB CODE: 11/ SUBM DATE: 21May64

Card 1/1

44147

s/181/62/004/010/037/063 B102/B112

24:1500

AUTHORS:

Yeliseyev, P. G., K'ang Ch'ang-ho, and Nakhodnova, I. A.

TITLE:

"Inherent" dislocations and the recombination in p-type

germanium

PERIODICAL: Fizika tverdogo tela, v. 4, no. 10, 1962, 2880-2884

TEXT: The recombination properties of what are called "inherent" dislocations are studied. These dislocations are understood to have formed dislocations are studied. These dislocations are understood to have formed during the growth of the Ge single crystal. They limit the surplus carrier lifetime  $T = 1/\sigma_R N$ ; wherein  $\sigma_R$  is the recombination efficiency of the dislocations and on dislocations depending on the type and genesis of the dislocations and on the position of the Fermi level. If foreign recombination centers exist the position of the Fermi level. If foreign recombination centers exist then  $1/T = \sigma_R N + 1/\widetilde{\iota}_f$ . The recombination properties of p-type Ge single crystals grown according to the Czochralski method and having dislocation crystals grown according to the Czochralski method and having dislocation densities between 0 and 10 cm<sup>-2</sup> were studied by measuring the temperature dependence of T. The dislocation density was determined by counting the etching grooves (KOH+K<sub>3</sub>Fe(CN)<sub>6</sub> etching agent), T was measured by a Card 1/3

S/161/62/004/010/037/063 B104/B112

"Inherent" dislocations and the ...

compensation method according to the photogal vanometric effect and the photoconductivity. No adhesion effects were observed. The measurements were made in two series. The mean resistivities of the crystals in the first series were 7.7 ohm.cm, those of the second series 1.8 ohm.cm. For these two resistivities  $\sigma_R = 0.17$  and 0.33 cm²/sec. Crystals without dislocations and crystals with dislocation densities up to  $10^3$  cm² showed notably different curves '(T)' curves.  $\mathcal{T} = \mathcal{T}_1 + \mathcal{T}_2^2 \exp(-E/kT)$  can be written where  $\mathcal{T}_{1,2}$  and E are constants. E denotes the depth of recombination level position, i. e., 0.10 - 0.12 ev. The recombination properties of the inherent dislocations are proved to be closely similar to the dislocations produced by deformations. At room temperature,  $\sigma_R$  is in agreement with the data given in FTT, 2, 1542, 1960. With decreasing temperature it increases, however, according to a law somewhat different from those found earlier. A low temperatures the temperature dependence of Universitals with dislocation densities below  $10^3$  cm² is only slight. There are 3 figures and 1 table.

Card 2/3

"Inherent" dislocations and the ... S/181/62/004/010/037/063
B102/B112

ASSOCIATION: Moskovskiy gosudarstvennyy universitet im. M. V.
Lomonosova (Moscow State University imeni M. V.
SUBMITTED: June 2, 1962

ACCESSION NR: AP4039689 S/0181/64/006/006/1900/1902

AUTHOR: Yunovich, A. E.; Yeliseyev, P. G.; Nakhodnova, I. A.;
Ormont, A. B.; Osadchaya, L. A.; Stuchebnikov, V. M.

TITLE: Radiative recombination in Zn-diffused GaAs p-n junctions

SOURCE: Fizika tverdogo tela, v. 6, no. 6, 1964, 1900-1902

TOPIC TAGS: recombination radiation, radiative recombination, electroluminescence, p n junction, GaAs laser, GaAs diode, semi-conductor laser, laser, junction laser, injection laser

ABSTRACT: Recombination radiation from Be-doped GaAs p-n junctions was investigated with a view toward possible laser application of Be-doped GaAs injection diodes. The GaAs with a carrier concentration between 5·10<sup>17</sup> and 10<sup>18</sup> cm<sup>-3</sup> was diffused with Be in vacuum at 950C. The junction was about 3·10<sup>-3</sup> cm<sup>2</sup>. In one of the diodes the junction was 30 µ deep. Two parallel planes were cleaved perpendictular to the junction. The recombination radiation spectra were obtained by injecting carriers with current pulses up to 100 amp.

The pulse duration was 1.2 µsec and the repetition rate was 50 cps.

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# ACCESSION NR: AP4039689

The recombination spectra at 77K show that the intensity of emission is very similar to that of Zn-doped GaAs diodes. The maximum occurs of 1.47 ev. The line width at half maximum and at a current density of 2.8·10³ amp/cm² was 0.014 ev. Some narrowing and nonlinear increase intensity were observed at high current densities. Analysis of current-voltage characteristics and recombination spectra shows that found to be greater than 10¹8 cm³. Radiative recombination in Bedoped GaAs has a higher degree of probability than in GaAs doped with transitions between the conduction band and the acceptor levels, the ling of the line was believed to be caused by stimulated emission, degenerate GaAs doped with Be. Orig. art. has: 2 figures.

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ASSOCIATION: Moskovskiy gosudarstvennyky universitet im. H. V. Lomonosova (Moscow State University)

Card 2 / 3

"APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R001136020

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# "APPROVED FOR RELEASE: Monday, July 31, 2000

CIA-RDP86-00513R001136020

APPROVED FOR RELEASE: Monday, July 31, 2000 CIA-RDP86-00513R001136  LACC P.R. AP6026678  AUTHOR: Vavilov, V. S.; Nakhodnova, I. A.; Silin', A. R.; Yunovich, A. E.  AUTHOR: Vavilov, V. S.; Nakhodnova, I. A.; Silin', A. R.; Yunovich, A. E.  TITLE: Radiative recombination of GaSb p-n junctions obtained by crystal pulling from a melt universitet)  TOPIC TAGS: gallium antimonide, single crystal growing, recombination spectrum, crystal donor, crystal impurity, proceedings from a melt alloyed with an acceptor (Zn, ABSTRACT: p-n junctions in single crystals of GaSb were obtained by growing a crystal of containing a donor (To) (or acceptor) impurity from a melt alloyed with an acceptor (Scale Color respectively donor) impurity. The crystals were grown in a hydrogen atmosphere (Cd) (or respectively donor) impurity. The crystals were grown in the concentration is devoted to the The seeds were oriented along the direction (11). Primary attention is murities in the arm pendence of the radiative recombination spectra on the concentration levels (current defendence of the radiative recombination spectra on the concentration levels (current and of the p-n junction and on the injection level. In particular, low excitation levels of the p-n junction and on the injection was observed at small currents and large concentration of about 1 a/cm <sup>2</sup> ) were investigated. The dependence of energy at the emission spectral peak on the voltage across the p-n junction was observed at small currents and large concentration the voltage across the p-n junction was observed at small currents.
ORG: Moscow State University im. M. V. Lomonosov (Mossive Universitet)  TITLE: Radiative recombination of GaSb p-n junctions obtained by crystal pulling from a melt universitet:  TITLE: Radiative recombination of GaSb p-n junctions obtained by crystal pulling from a melt source: Fizika tverdogo tela, v. 8, no. 8, 1966, 2330-2335  SOURCE: Fizika tverdogo tela, v. 8, no. 8, 1966, 2330-2335  TOPIC TAGS: gallium antimonide, single crystal growing, recombination spectrum, crystal donor, crystal impurity, produced containing a donor (Te) (or acceptor) impurity from a melt alloyed with an acceptor donor.  ABSTRACT: P-n junctions in single crystals of GaSb were obtained by growing a crystal on a melt alloyed with an acceptor (Zn, donor) impurity from a melt alloyed with an acceptor december of the donor of t
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ORG: Moscow State outlines of GaSb p-n junctions obtained by crystal part of universitet)  TITLE: Radiative recombination of GaSb p-n junctions obtained by crystal part of GaSb p-n junctions obtained by crystal part of GaSb p-n junctions of GaSb p-n junctions obtained by growing a crystal on a donor, crystal impurity, pn junctions in single crystals of GaSb were obtained by growing a crystal on a donor, crystal impurity, pn junctions in single crystals of GaSb were obtained by growing a crystal on a donor. The crystals were grown in a hydrogen atmosphere.  ABSTRACT: p-n junctions in single crystals were grown in a hydrogen atmosphere.  Primary attention is devoted to the area condendation of impurities in the area condendation.
TITLE: Radiative recombination of Gaso P  SOURCE: Fizika tverdogo tela, v. 8, no. 8, 1966, 2330-2335  TOPIC TAGS: gallium antimonide, single crystal growing, recombination spectrum, crystal on a donor, crystal impurity, production of Gaso were obtained by growing a crystal on a donor, crystal impurity, production in single crystals of Gaso were obtained by growing a crystal on a donor, crystal impurity, production in single crystals of Gaso were obtained by growing a crystal on a donor, crystal impurity from a melt alloyed with an acceptor (Zn, and containing a donor (Te) (or acceptor) impurity from a melt alloyed with an acceptor decorption of impurities in the area containing a donor (Te) (or acceptor) impurity.  The crystals were grown in a hydrogen atmosphere.  Primary attention of impurities in the area concentration of impurities in the area concentration of impurities in the area.
TITLE: Radiative recombination of Gaso P  SOURCE: Fizika tverdogo tela, v. 8, no. 8, 1966, 2330-2335  TOPIC TAGS: gallium antimonide, single crystal growing, recombination spectrum, crystal on a donor, crystal impurity, proportion of Gaso were obtained by growing a crystal on a donor, crystal impurity, proportion in single crystals of Gaso were obtained by growing a crystal on a donor, crystal impurity, proportion impurity from a melt alloyed with an acceptor (Zn, abstract: P-n junctions in single crystals were grown in a hydrogen atmosphere.  ABSTRACT: P-n junctions in single crystals were grown in a hydrogen atmosphere.  The crystals were grown in a hydrogen atmosphere are grown in a hydrogen atmosphere.  Primary attention is devoted to the area concentration of impurities in the area concentration of impurities in the area.
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tron trans	trations of impurities. This dependence is apparently due to the tunnel effect, inc tron transitions to the "tail" of the density curve of the states of the conduction ba art. has: 5 figures.							
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NAKHRADYAN, A.A., inzh.; BARINSKIY, B.D.

Utilizing the possibilities for curtailing idle time of reilrosd cars. Zhel. dor. transp. 40 no. 7:72 Jl '58. (MIRA 11:7)

1. Nachal'nik stantaii Bessarabskaya(for Nakhradyan). 2. Zamestitel' nachal'nika stantaii Bessarabskaya(for Barinskiy).

(Railroada--Management)

ACC NR. AP7006472

SOURCE CODE: UR/0415/66/000/004/0100/0102

AUTHOR: Andriyevich, V. V.; Mogilevskaya, S. Ye.; Nakhrov, S. T.; Starkov, G. P.

ORG: Eastern Scientific Research Mining Institute (VostNIGRI), Novokuznetsk (Vosto-chnyy nauchno-issledovatel'skiy gornorudnyy institut [VostNIGRI])

TITLE: On the relationship between the velocity of a longitudinal ultrasonic wave and the strength of rock and ore in the Sheregesh deposit (Cornaya Shoriya)

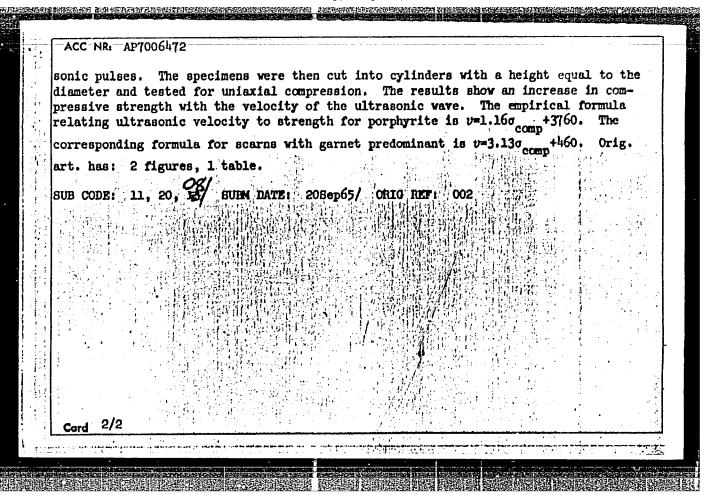
BOURCE: Fiziko-tekhnicheskiye problemy razrabotki poleznykh iskopayemykh, nc. h, 1966, 100-102

TOPIC TAGS: ultrasonic wave propagation, compressive strength, mining engineering

ABSTRACT: The article is a report on studies being conducted in the Geological Laboratory of the Eastern Scientific Research Mining Institute to establish the relationship between the velocity of longitudinal ultrasonic waves and the compressive strength of rock and ore. Limestone and porphyrite specimens from the Sheregesh deposit with a fairly constant mineralogical composition and consistent structural characteristics were studied together with skarns and ores. An IPA-59 seismoscope was used for determining the velocity of an ultrasonic wave in cylindrical specimens 100-160 mm long and 32-56 mm in diameter. Rochelle salt piezoelectric pickups with a natural oscillation frequency of 250 kc were used as emitter and receivers of ultra-

Card 1/2

UDC: 552.1:53(571.17)



KAZANTSEV, F.N., kand.med.nauk; NAKHROVA, Z.V.

External respiration in scoliosis. Ortop., travm. i protez. 25 no.5:33-36 My 164. (MIRA 18:4)

1. Iz anesteziologicheskogo otdeleniya (rukovoditeli - F.N. Kazantsev) Kazanskogo instituta travmatologi i ortopedii (dir. - starshiy nauchnyy sotrudnik U.Ya.Rogdanovich). Adres avtorov: Kazani 15, ul. M.Gorikogo, d.3, Institut travmatologii i ortopedii.

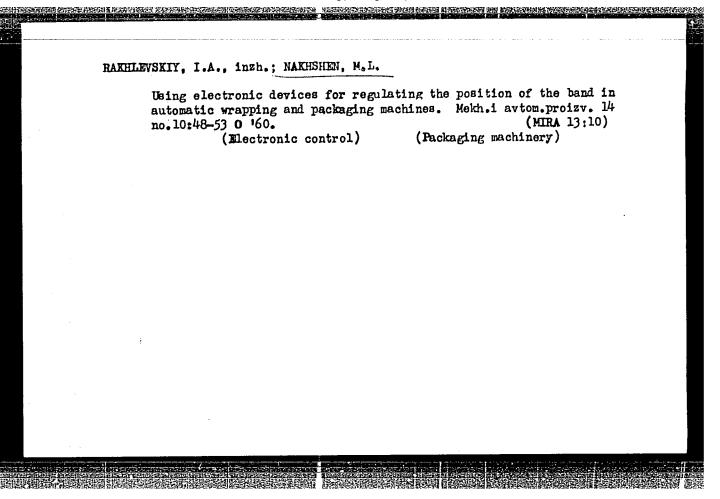
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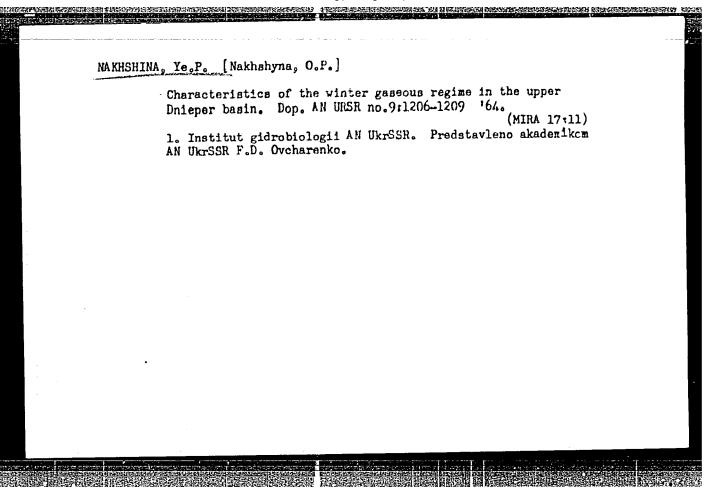
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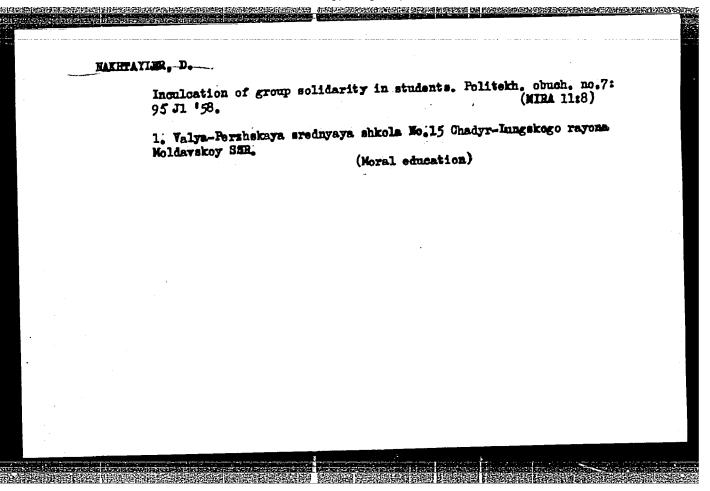
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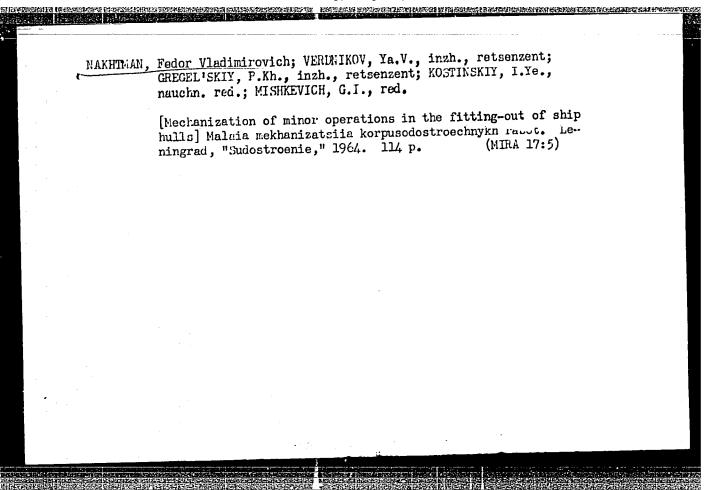
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1. Iz Kazanskogo instituta travmiteicgii i ortopedii (dir. - starshiy nauchnyy sotrudnik U.Ya. Eogdanovich).









ROTATION CONTRACTOR IN THE PROPERTY OF THE PRO

# Experience in coating propeller blades with rubber compositions Mor.flot 16 no.4:27-28 A 156. (MLRA 9:8)

1. Starshiy tekhnolog mekhanicheskogo tsekha zavoda imeni Parizhskoy Kommuny.

(Propellers--Corrosion)

NEWSTRAND DESCRIPTION OF THE PROPERTY OF THE P

NAKHUPINA, A. G., Cand of Agric Sci -- (diss) "Russian white chickens pf the Kuchinskiy Fowl Sovkhoz; their productivity and breeding qualities." Moscow, 1957, 22 pp (Moscow Veterinary Academy), 140 copies (KL, 32-57, 95)

Listuation will disconnect the second tm/o044/65/000/004/B030/B030 ACCESSION NR: AR5013623 517.912 SOURCE: Ref. zh. Matematika, Abs. 4B149 C AUTHOR: Nakhushey. A. M. TITLE: Concerning the integration of the generalized Niccati equation in quadrature CITED SOURCE: Uch. zap. Kabardino-Balkarak. un-t. Ser. fiz.-maten. n., vyp. 19, 1963, 325-328 TOPIC TAGS: Riccati equation, integration, generalized equation, quadrature TRANSLATION: The sixthor defines a generalized Riccati equation of order  $\lambda$  by means of the formula  $A_i = E(z)A_y + \delta(z)A + S(z)$ (1)The quantity x, defined by the formula x = (PB' - RP')/PQRCard 1/2

ACCESSION	NR: AR50136	23		<u>.</u>
cally, Eq	. (1) is called quadratures.	dex of Eq. (1). In the ireduced. It is prove The conditions for the need in the case of acceptanting the value of	ed that the reduced a solvability in qua a particular assumpt	'equation can be adratures of the Lions concerning
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ACC NR: AP6031642

SOURCE CODE: UR/0020/66/170/001/0038/0040

AUTHOR: Nakhushev, A. M.

ORG: Mathematics Institute of the Siberian Department of the Academy of Sciences

SSSR (Institut matematiki Sibirskogo otdeleniya Akademii nauk SSSR)

TITLE: A boundary value problem for a mixed equation having two lines of degeneracy

SOURCE: AN SSSR. Doklady, v. 170, no. 1, 1966, 38-40

TOPIC TAGS: partial differential equation, boundary value problem, Fredholm equation, integral equation

ABSTRACT: 'The following equation is studied

$$y(y-1)u_{xx}+u_{yy}=0$$

in a specially constructed mixed region containing intervals of the lines of degeneracy y = 0 and y = 1. A boundary value problem connected with this equation is formulated and the solution sketched. It is shown that the problem of the existence of a solution reduces to the solution of a system of singular integral equations which may be reduced to a Fredholm equation of the second order, and that the solution of the boundary value problem may, after the Fredholm equation is solved, be constructed by solving Trikomi's singular problem. Orig. art. has: 12 formulas.

SUB CODE:

SUBM DATE: 15Dec65/

ORIG REF: 004/

OTH REF: 003

UDC: 517,946

MAKHGFIN, +.

27-4-7/25

AUTHOR: Nakhutin, I., Director of the Leningrad Municipal Methodical-

Educational Laboratory

TITLE: A Group of Mechanic Foreman's Experiment in Improving the Work

Locale (Opyt usovershenstvovaniya rabochego

mesta mastera gruppy slesarey)

PERIODICAL: Professional'no-Tekhnicheskoye Obrazovaniye, 1958, # 4,

pp 14-16 (USSR)

ABSTRACT: While inspecting a number of Leningrad factory schools, the

author saw that one of the great lacks is still training aids. Last summer, he went to Czechoslovakia and was greatly impressed by the facilities, quality of instruction and the amount and type of training aids and equipment, especially a new teacher's

tool cabinet he saw.

There is one table, and a 2-page center-spread.

ASSOCIATION: Leningradskiy gorodskoy uchebno-metodicheskiy kabinet (Leningrad

Municipal Methodological-Educational Laboratory)

AVAILABLE: Library of Congress

Card 1/1

AUTHOR: Nakhutin, I., Head of the Workshop SOV/27-59-1-14/31

TITLE: Higher-Quality Training of Construction Workers (Vyshe

kachestvo podgotovki stroiteley)

PERIODICAL: Professional no-tekhnicheskoye obrazovaniye, 1959, Nr 1,

pp 19-21 (USSR)

ABSTRACT: The author refers to the 7-year-plan and to the construc-

tion projects during that period. He especially deals with the reequipping and modernization of construction and trade schools. Finally he comments on model school

workshops and equipment. There is one sketch.

ASSOCIATION: Leningradskiy gorodskoy uchebno-metodicheskiy kabinet

(The Leningrad Municipal Methodic-Training Workshop)

Card 1/1

•	NAKHUTIN, I.; MEKKEL', A., prepodavatel'; NAZARENKO, G., inzh.
	New visual aids for the training of plasterers, painters, and glaziers. Proftekh.obr. 18 no.2:14-16 F '61. (MIRA 14:3)
and the summarism.	<ol> <li>Direktor remeslennogo uchilishcha No. 42, Leningrad (for Nakhutin).</li> <li>Remeslennoye uchilishche No.42, Lenigrad (for Nazarenko).</li> <li>(Building trades—Audio-visual aids)</li> </ol>
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<u>.</u>	

NAKHUTIN, Isaak Pinkhusovich; GAVRILOV, F.P., red.; PERSON, M.N., tekhn.

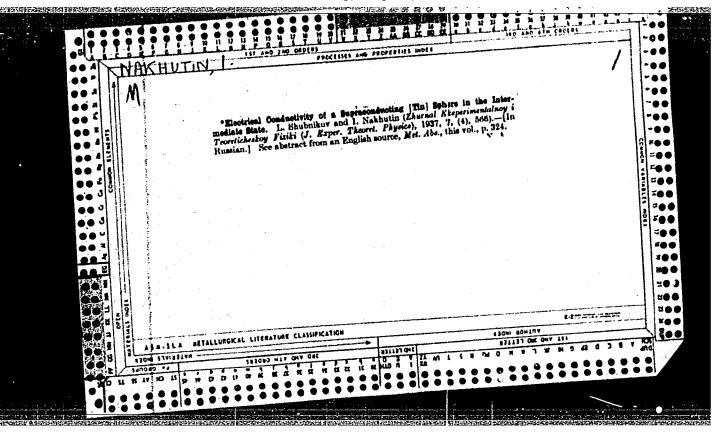
[Equipment of a study room for machining on lathes; album of technical drawings of a special-purpose cupboard and visual aids] Oborudovanie kabinate po tokarnomu delu; al'bom rabochikh chertezhei spetsial'nogo shkafa i nagliadnykh posobii. Moskva, Vses. uchebno-pedagog. izd-vo Trudrezervizdat, 1959. 415 p. (MIRA 14:9) (Turning-Study and teaching)

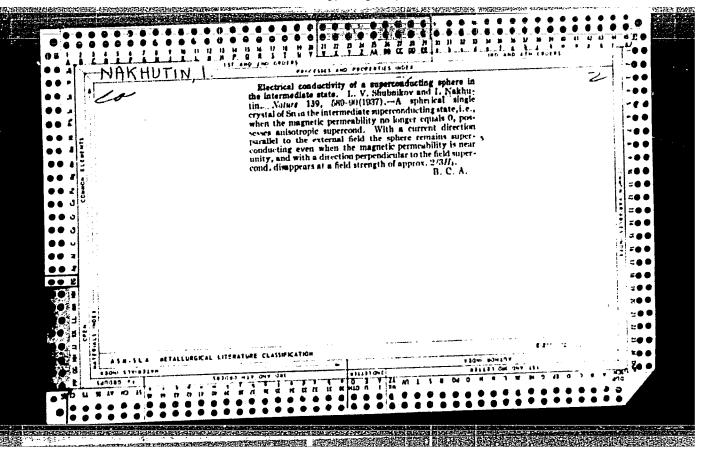
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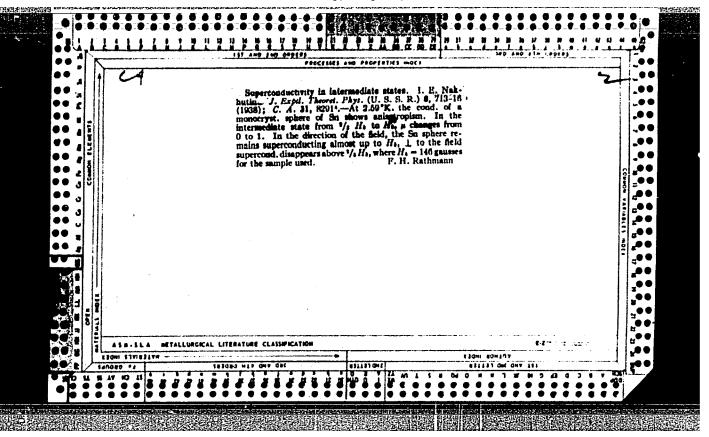
NAKHUTIN, Isaak Pinkhusovich; KUZNETSKIY, Gennadiy Ivanovich; SMIRNOV,
B.V., nauchnyy red.; KOBRINSKAYA, M.V., red.; NESMYSIOVA, L.M.,
tekhn. red.

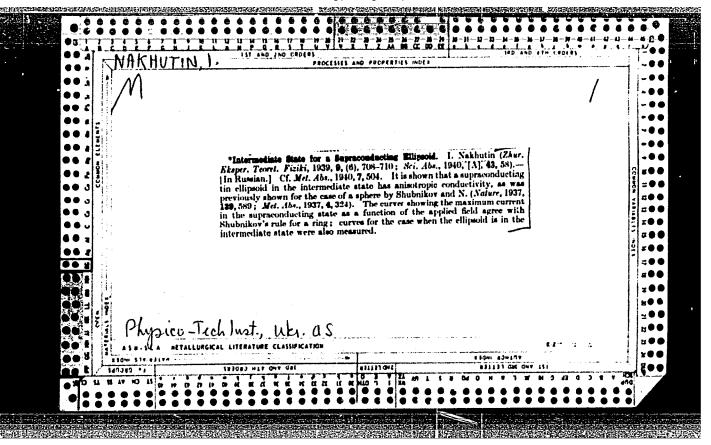
[Manual on practical problems in electrical engineering] Posobie dlia
prakticheskikh zaniatii po elektrotekhnike. Moskva, Vses. uchebnopedagog. izd-vo Proftekhizdat, 1961. 66 p. (MIRA 14:8)

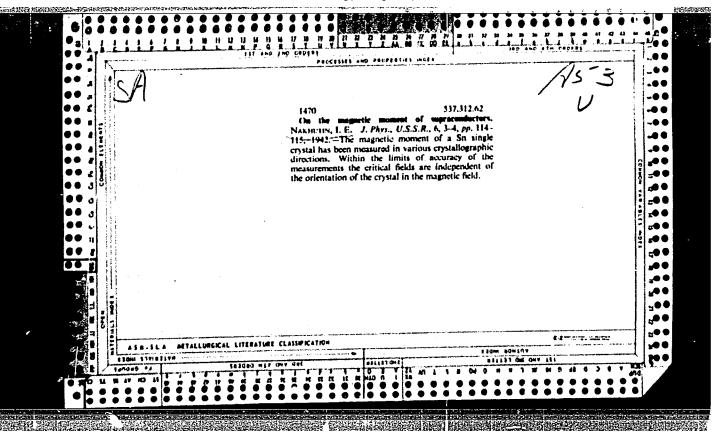
(Electric engineering—Handbooks, manuals, etc.)











The magnetic behaviour of supraconducting alloys of Sh-Zh. Lazarey, B. G. AND NARMITIN. F. J. Phys., U.S.S.R., 6, 3-4, p. 116-119, 1942.—The critical fields and temperatures of the alloys coincide with those for Sh. Very small particles of Sh which could change the critical fields are not present in the alloys in any noticeable quantity. In low fields the curves for the magnetic moment of the investigated alloys, and even of the alloy containing 10% of Sh, do not differ from the curves for the pure supraconductor.	The magnetic behaviour of supraconducting alloys of Sn-Zn, LAZAREY, B. G. AND NAKHUTUN I. E. J. Phys., U.S.S.R., 6, 3-4, pp. 116-119, 1942.—The critical fields and temperatures of the alloys coincide with those for Sn. Very small particles of Sn which could change the critical fields are not present in the alloys in any noticeable quantity. In low fields the curves for the magnetic moment of the investigated alloys, and even of the alloy containing the	rin, I. je.	en e	in the state of the state and all the processors who have processors and the state of the state		
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	Physico-Tech. lust. AS Ukr SSR					

12.7530 507/126-7-3-31/44

AUTHORS: and Sutyagina, Ye. I.

Absorption of Hydrogen by Palladium at Low Temperatures TITLE: (Pogloshcheniye vodoroda palladiyem pri nizkikh temperaturakh)

PERIODICAL: Fizika metallov i metallovedeniye, Vol 7, Nr 3, p 459 (USSK)

ABSTRACT: The rapid absorption of hydrogen by platinum black has enabled the authors to measure the isotherm of hydrogen absorption by palladium at - 78°C. In Fig.1 the results of three series of measurements are shown. The initial portion of the curve corresponds to the a-phase of the hydrogen-palladium solid solution; a horizontal portion of two-phase region follows, and the last portion rises steeply and corresponds to the phase of the solid solution. The pressure at which the phase transformation occurs is 0.015-0.018 mm Hg. The quantity of hydrogen dissolved at this pressure in the -- phase is 70-71 n. cm<sup>3</sup>/g Pd. At a pressure of 13 mm Hg the quantity about 82 n. cm<sup>3</sup>/g Pd. At - 120°C and of dissolved hydrogen is about 82 n. cm

(H/Pd = 0.78).Card 1/2 pressure of about 15 mm Hg the quantity of dissolved

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Absorption of Hydrogen by Palladium at Low Temperatures

hydrogen attained 86 n. cm<sup>3</sup>/g Pd ( H / Pd 0.82). At - 196°C absorption of hydrogen proceeded very slowly The experiments, carried out in a closed circuit containing a given quantity of hydrogen and palladium, showed that the hydrogen absorption still continued after two days. The concentrations of hydrogen dissolved in palladium remained lower than those at - 78°C at the same pressures. It follows that the hydrogen-palladium system had not reached equilibrium as the solubility of hydrogen in palladium must increase with drop in temperature. There is 1 figure, and 4 references of which 2 are Soviet and 2 English.

SUBMITTED: September 2, 1957

Card 2/2

SOV/120-59-1-44/50

AUTHORS: Nakhutin, I. Ye., Smirnova, N. M.

TITLE: Production of Pure Xenon (Polucheniye chistogo ksenona)

PERIODICAL: Pribory i tekhnika eksperimenta, 1959, Nr 1, p 149 (USSR)

ABSTRACT: A method of separating the hydrocarbons present in xenon is described. The elimination of the hydrocarbons was done by employing a highly active reagent which is prepared by depositing a layer of copper oxide on a surface of silica gel. The reagent was placed in a short quartz tube (having a length of a few cm), and dehydrated at a temperature of 300°C. The tube was then heated to 700°C, and the xenon to be purified was passed through it. The device operated as a chromatographic column in that the change of colour of the reagent after the reaction permitted the observation of the front forming in the column. A preliminary filling of the column by xenon was done very slowly. Subsequently, the xenon was passed in a continuous stream, at a rate of about 10 L/cm2hr. through the heated column and through another two columns operating at the ambient temperature. The other two columns captured the carbonic acid and the water vapours which formed during the oxidation of the hydrocarbons. After the operation the column was regenerated at 600°C. By the above method Card 1/2 it was possible to obtain a spectrally pure xenon; the lines

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THE CONTROL OF THE CO

Production of Pure Xenon

of hydrogen and oxygen could not be detected, nor were the molecular spectra of hydrocarbons present. The method can be used for the purification of other rare gases. The authors express their gratitude to N. A. Teterina for carrying out the spectral analysis. There are no figures or references.

SUBMITTED: February 15, 1958.

Card 2/2

84.397

**s/056/60/**030/004/015/048 B004/B070

24.6720 AUTHORS:

Nakhutin, I. Ye., Ovechkin, V. V., Ochkin, D. V.,

Polyakov, A. S., Khoduleva, Z. K.

TITLE:

Preparation of the Radioactive Isotope  $\frac{Kr^{35}}{9}$  and Investigation of Its Gamma Radiation

PERIODICAL:

Zhurnal eksperimental noy i tecreticheskoy fiziki, 1960,

Vol. 39, No. 4(10), pp. 991-992

Kr35 was obtained by dissolving neutron-irradiated uranium in nitric acid and by separating chromatographically by active carbon at 77°K the gases liberated from moisture, nitrogen oxides, and radioactive iodine. For the measurement of emission, Kr35 was filled in a plexiglass cylinder with an aluminum foil bottom. The yield was determined from the ratio  $k_{\gamma} = N_{\gamma}/N_{\beta}$ , where  $N_{\gamma}$ ,  $N_{\beta}$  are, respectively, the numbers of 517 kev gamma quanta and of  $\beta$  particles emitted per unit time in the solid angle  $4\pi$ . The beta radiation was measured by an CM-2B (SI-2B) counter, and the gamma radiation by a NaI(T1) scintillator

Card 1/2